Evaluates: MAX25611A/MAX25611B/ MAX25611C/MAX25611D

General Description

The MAX25611 evaluation kit (EV kit) provides a proven design to evaluate the MAX25611A/MAX25611B/ MAX25611C/MAX25611D automotive high-voltage, highbrightness LED (HB LED) controller. The EV kit is set up for boost and buck-boost configurations and operates from a 6V to 18V DC supply voltage. The EV kit is configured to deliver up to 0.88A to one string of LEDs. The total voltage of the string can vary from 3V to 36V. The anode of the LED string should be connected to the LED+ terminal. The cathode of the LED string can be connected either to GND (boost mode) or IN (buck-boost mode). In the case of boost mode, the input voltage should not exceed the LED string voltage.

Benefits and Features

- Configured for Boost and Buck-Boost Application
- Analog Dimming Control
- Proven PCB Layout
- Fully Assembled and Tested Feature

Ordering Information appears at end of data sheet.

Quick Start

Required Equipment

- MAX25611 EV kit
- 12V, 5A DC power supply
- A series-connected LED string rated at least 1A
- Oscilloscope with a current probe

Procedure

The EV kit is fully assembled and tested. Follow the steps below to verify board operation. **Caution: Do not turn on power supply until all connections are made.**

- 1) Verify that all jumpers (J1, J2, and J7) are in their default positions, as shown in <u>Table 1</u>.
- 2) Connect the positive terminal of the 12V supply to the VIN PCB pad and the negative terminal to the nearest GND PCB pad.
- 3) Connect the LED string across the LED+ and LED-PCB pads on the EV kit for buck-boost configuration. For boost configuration, connect the LED string across the LED+ and GND PCB pads on the EV kit. The LED string voltage should be higher than the input voltage in this configuration.
- 4) Clip the current probe on the wire connected to the LED string.
- 5) Turn on the DC power supply.
- 6) Verify that the LEDs turn on.
- 7) Verify that the oscilloscope displays approximately 0.88A.



Evaluates: MAX25611A/MAX25611B/ MAX25611C/MAX25611D

Detailed Description

The MAX25611 EV kit provides a proven design to evaluate the MAX25611A/MAX25611B/MAX25611C/ MAX25611D high-voltage HB LED driver with integrated high-side current sense. The EV kit is set up for boost and buck-boost configurations and operates from a 6V to 18V DC supply voltage. The string-forward voltage can vary from 3V to 36V. The EV kit is optimized for 0.8A and a series of 8 LEDs in a string. Other configurations may require changes to component values.

Analog Dimming Control (REFI)

When J2 is installed across pins 1-2, the LED current is set at the maximum current. The REFI pin is connected to VCC and in this case, the LED current is given by the following equation:

$$I_{LED} = \frac{220 \text{mV}}{\text{R14}}$$

In the case of the EV kit, I_{LED} is set to 0.88A.

When J2 is installed across pins 2-3, the REFI pin is connected to the voltage-divider of R1 and R2, which sets the REFI voltage. If V_{REFI} < 1.2V, then V_{REFI} sets the LED current level.

$$I_{LED} = \frac{\left(V_{REFI} - 0.2V\right)}{5 \times R14}$$

Table 1. MAX25611 EV Kit Jumper Descriptions

Alternatively, the analog dimming can be controlled by removing the shunt on J2 and applying a voltage between 0 and 5.5V on the REFI test point on the EV kit. REFI voltages above 1.3V are limited to an equivalent of 1.3V inside the IC.

Pulse-Dimming Input (PWMDIM)

The EV kit demonstrates the PWM dimming feature of the buck controller using either an external PWM signal, or a DC voltage at the DIM pin.

Analog-to-PWM dimming: Install a shunt across J1 (1-2). Adjust the potentiometer R18 to set a DC voltage on the PWMDIM pin. The PWM dimming duty cycle is set by the voltage at PWMDIM between 0.2V (0% duty) and 3V (100% duty). Alternatively, drive the PWMDIM testpoint with an external DC source. PWMDIM voltages above 3V set the dimming duty cycle to 100%.

Direct PWM dimming: Leave J1 open and connect a PWM signal to the PWMDIM testpoint. Vary the duty cycle to increase or decrease the intensity of the HB LED string. The PWMDIM input of the device has a 2V (max) rising threshold and a 0.8V (min) falling threshold and is compatible with 3.3V and 5V logic-level signals. Uninstall C2 to achieve fast PWMDIM rise and fall edges at the IC pin.

JUMPER	SHUNT POSITION	DESCRIPTION
J1	1-2*	Connects the PWMDIM pin of the device to VCC through a voltage divider formed by R13 and R18. The dimming duty cycle is adjusted from 0% to 100% for PWMDIM level between 0.2V and 3V. The dimming frequency is internally set at 200Hz.
	2-3	Connects the PWMDIM pin to ground to disable the analog dimming function and keep the IC off.
	Open	Connect an external function generator to drive the PWMDIM pin with a signal from 0 to 3.3V or higher. PWMDIM pulse width should be at least above one switching period. Recommended PWMDIM frequency range is from 200Hz to 2kHz for visible LEDs. IR LEDs can operate at lower frequencies where flicker is not visible.
J2	1-2*	Connects VCC to the REFI pin. LED current is at the maximum value of 0.88A in this configuration.
	2-3	Connects the REFI pin of the device to VCC through a voltage divider formed by R1 and R2. Adjusting R2 allows programming the LED current from 0 to 0.88A for REFI levels from 0.2V to 1.3V. For REFI voltages above 1.3V, the LED current is limited at 0.88A.
	Open	Connect an external voltage source to set the LED current from 0 to 0.88A for REFI levels from 0.2V to 1.3V. For REFI voltages above 1.3V, the LED current is limited at 0.88A.
J7	1-2*	Connects the IN pin to the same input supply as the boost power stage through a 10Ω filter resistor.
	Open	Connect an external supply voltage greater than 4.7V to J7 pin 2 to bias the IC IN pin.

*Default position.

Evaluates: MAX25611A/MAX25611B/ MAX25611C/MAX25611D

2.2MHz Operation

The EV kit can be used to evaluate 2.2MHz operation. To test the 2.2MHz application:

- Change the IC to MAX25611B (provided).
- Change L2 to 2.2µH.
- Change C9 to 0.22μF. R6 remains at 50Ω.
- Output capacitance can be reduced to 1x 4.7µF. Note that short pulse widths at low frequencies benefit from having higher total output capacitance to counter leakage currents that discharge the output voltage before the next pulse.
- Change other components as required (e.g., MOSFET, FET current sense R9, LED current sense R14).

High-Beam/Low-Beam Application

The EV kit can be used to evaluate high-beam/low-beam switching applications. Connect the low-beam LED string across LED+ and HB_LED+, and the high-beam LED string across HB_LED+ and GND. Use a function generator or a DC source to drive the HIGHBEAM_OFF pad to 5V or GND to disabled or enable the high-beam LEDs. Slew rate control of the driving signal, or adjustment of R19 and C17 values can be used to control the transition of the Q3 shunting FET to minimize surge currents through the low-beam LEDs.

Latch Circuit

The latch circuit proves HB+LED+ short-to-battery protection by disabling the shunt FET gate. This prevents the shunt FET from shorting out the battery. The latch is reset by removing power to recycle VCC.

Voltage Regulator Configuration

The EV kit can be reconfigured as a voltage regulator using R27 and R28 as the voltage feedback resistor divider, after removing R14.

$$V_{OUT} = \frac{\left(V_{REFI} - 0.2\right)}{5} \times \frac{\left(R27 + R28\right)}{R27}$$

Setting V_{REFI} = 1.2V selects a large feedback signal for better accuracy and noise immunity. For simplicity, select R27 to match the programmed regulation voltage across ISENSEP and ISENSEN. For example, with V_{REFI} = 1.2V, V(ISENSEP - ISENSEN) = 200mV, and R27 should be 200 Ω . This makes 1mV per Ω or 1mA down the resistor string, minimizing the error due to ISENSEN leakage current. The calculation for R28 is then simplified to (VOUT - 0.2) x 1000.

The following components should also be changed:

- Power stage components (Q1, L2, D1, R9 and output capacitance) as required for the application (voltage, current rating, etc).
- COMP components (R6, C9, C16) to match the application requirements.
- Remove C14, R17, and Q2.

Ordering Information

PART	ТҮРЕ
MAX25611EVKIT#	EV Kit

#Denotes RoHS compliance.

Evaluates: MAX25611A/MAX25611B/ MAX25611C/MAX25611D

DNI/DNP ITEM REF_DES MFG PART # MANUFACTURER VALUE DESCRIPTION QTY GRM32ER72A225KA35 MURATA;TDK; CAPACITOR; SMT (1210); CERAMIC CHIP; 2.2UF; 100V; TOL = 10%; 1 C1. C19 2 CGA6N3X7R2A225K230: 2.2UF YAGEO MODEL = GRM SERIES; TG = -55°C to +125°C; TC = X7R CC1210KKX7R0BB225 CAPACITOR; SMT (0603); CERAMIC CHIP; 0.01UF; 100V; TOL = 5%; 2 C2, C16 2 CGA3EANP02A103J080AC TDK 0.01UF _ MODEL = MULTILAYER CERAMIC CHIP CAPACITOR; TC = NPO CAPACITOR; SMT (CASE_F); ALUMINUM-ELECTROLYTIC; 22UF; 3 PANASONIC C3 1 EEE-TG2A220UP 22UF 100V: TOL = 20%: MODEL = TG SERIES: TG = -40°C TO +125°C C4, C5, CGA6M3X7S2A475K200AE CAPACITOR; SMT (1210); CERAMIC CHIP; 4.7UF; 100V; 4 6 4 7UF C11-C13, C15 CGA6M3X7S2A475K200AB TOL = 10%; TG = -55°C TO +125°C; TC = X7S; AUTO CAPACITOR; SMT (0603); CERAMIC CHIP; 4.7UF; 10V; 5 C6 _ 1 C1608X6S1A475K TDK 4.7UF TOL = 10%; TG = -55°C TO +105°C; TC = X6S GCJ188R71H104KA12: MURATA; CAPACITOR; SMT (0603); CERAMIC CHIP; 0.1UF; 50V; C7. C8 2 GCM188R71H104K: 0.1UF 6 MURATA:TDK TOL = 10%; TG = -55°C TO +125°C; TC = X7R; AUTO CGA3E2X7R1H104K080AA GCM188R71C105KA64; CAPACITOR; SMT (0603); CERAMIC CHIP; 1UF; 16V; TOL = 10%; 7 C9 _ 1 MURATA;TDK 1UF CGA3E1X7R1C105K080AC TG = -55°C TO +125°C; TC = X7R; AUTO CAPACITOR: SMT (0603): CERAMIC CHIP: 1000PF: 50V: GRM1885C1H102.JA01 MURATA;TDK 8 C10 1 1000PF C1608C0G1H102J080 TOL = 5%: TG = -55°C TO +125°C CAPACITOR; SMT (0603); CERAMIC CHIP; 100PF; 100V; 9 C14 1 C0603C101K1GAC KEMET 100PF _ TOL = 10%; MODEL = COG; TG = -55°C TO +125°C; TC = CAPACITOR: SMT (0603); CERAMIC CHIP; 4700PF; 100V 10 C17 C0603X472J1GAC KEMET 4700PF 1 TOL = 5%; MODEL = FT-CAP; TG = -55°C TO +125°C; TC = C0G 11 KEMET C20 1 C0805C104J1RAC 0 1UF CAP: SMT (0805): 0.1UF: 5%: 100V: X7R: CERAMIC CHIF CAPACITOR; SMT (0603); CERAMIC CHIP; 0.1UF; 100V; 12 C21 _ 1 CGA3E3X7S2A104K080AB TDK 0.1UF TOL = 10%; TG = -55°C TO +125°C; TC = X7S DIODES 13 D1 1 DFLS2100 DFLS2100 DIODE: SCH: SMT (POWERDI-123): PIV = 100V: IF = 2A _ INCORPORATED DIODES 14 D2 1 1N4148WS-7-F 1N4148WS-7-F DIODE; SWT; SMT (SOD-323); PIV = 75V; IF = 0.3A INCORPORATED DIODES DIODE; SWT; SMT (SOD-123); PIV = 100V; 15 D5 1N4148W-7-F 1N4148W-7-F 1 INCORPORATED IF = 0.3A; -65°C TO +150°C INDUCTOR; SMT (1210); FERRITE-BEAD; 52; 16 FB1 1 HE70ACB322513 TDK 52 _ TOL = ±25%; 0.4A; -40°C TO +125°C GND. HB LED+ EVK KIT PARTS: MAXIM PAD: WIRE: NATURAL: SOLID: 17 HIGHBEAM_OFF, J3-J6, 11 9020 BUSS WEICO WIRE MAXIMPAD WEICO WIRE: SOFT DRAWN BUS TYPE-S: 20AWG LED+, LED-, VCC, VIN CONNECTOR; MALE; THROUGH HOLE; BREAKAWAY; 18 PCC03SAAN SULLINS PCC03SAAN J1. J2 _ 2 STRAIGHT THROUGH; 3PINS; -65°C TO +125°C CONNECTOR: MALE: THROUGH HOLE: BREAKAWAY: 19 J7 _ 1 PCC02SAAN SULLINS PCC02SAAN STRAIGHT THROUGH; 2PINS; -65°C TO +125°C INDUCTOR; SMT; FERRITE BOBBIN CORE; 4.7UH; 20 L1 1 MSS1278T-472ML COILCRAFT 4.7UH _ TOL = ±0.2; 6.2A; -40°C TO +125°C 21 L2 1 MSS1278T-153ML COILCRAFT 15UH INDUCTOR; SMT; FERRITE; 15UH; 20%; 4.9A MACHINE FABRICATED; ROUND-THRU HOLE SPACER; 22 MH1-MH4 4 9032 **KEYSTONE** 9032 _ NO THREAD: M3.5: 5/8IN: NYLON 23 SQJA86EP-T1_GE3 VISHAY SILICONIX SQJA86EP-T1_GE3 TRAN; NCH; SO-8L; PD-(48W); I-(30A); V-(80V) Q1 1 TRAN; P-CHANNEL POWER TRENCH MOSFET; PCH; FAIRCHILD 24 02 _ 1 FDC3535 FDC3535 SEMICONDUCTOR SSOT-6; PD-(1.6W); I-(-2.1A); V-(-80V)

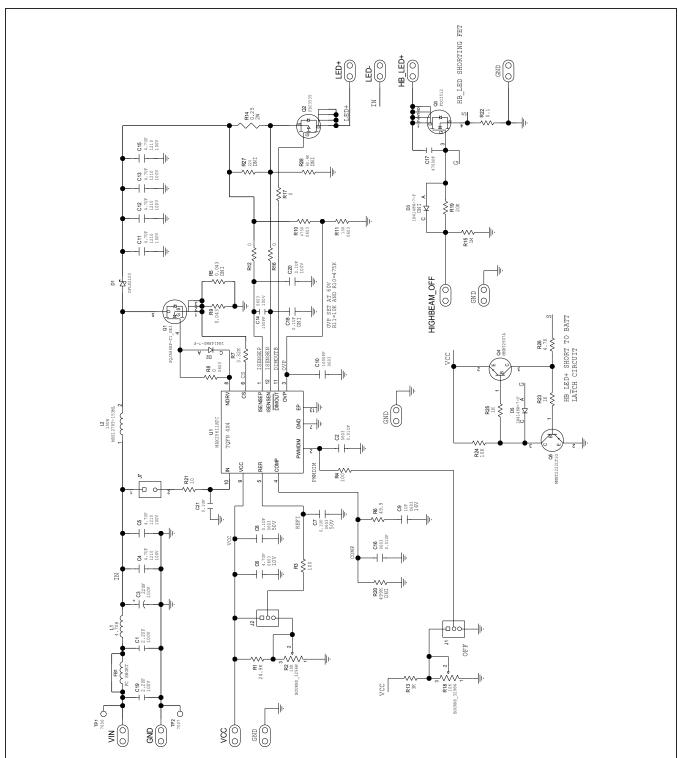
MAX25611 EV Kit Bill of Materials

Evaluates: MAX25611A/MAX25611B/ MAX25611C/MAX25611D

ITEM REF_DES DNI/DNP QTY MFG PART # MANUFACTURER VALUE DESCRIPTION TRAN; N-CHANNEL POWERTRENCH MOSFET; NCH; 25 Q3 FDC3512 ON SEMICONDUCTOR FDC3512 1 _ SUPERSOT-6; PD-(1.6W); I-(3A); V-(80V) FAIRCHILD TRAN: SMALL SIGNAL TRANSISTOR: PNP: SOT-23: 26 Q4 1 MMBT2907A MMBT2907A SEMICONDUCTOR PD-(0.35W); IC-(-0.6A); VCEO-(-60V) ON SEMICONDUCTOR MMBT2222LT1G 27 Q5 MMBT2222LT1G TRAN: NPN: SOT-23: PD-(0.225W): I-(0.6A): V-(30V) 1 _ 28 R1 CRCW060324K9FK VISHAY DALE 24.9K RESISTOR; 0603; 24.9KQ; 1%; 100PPM; 0.10W; THICK FILM RESISTOR: THROUGH-HOLE-RADIAL LEAD: 3296 SERIES 29 R2. R18 2 3296W-1-103LF BOURNS 10K 10KΩ; 10%; 100PPM; 0.5W; SQUARE TRIMMING POTENTIOMETER; _ 25 TURNS; MOLDER CERAMIC OVER METAL FILM CRCW0603100RFK: VISHAY DALE; RESISTOR; 0603; 100Ω; 1%; 100PPM; 0.10W; THICK FILM 30 R3. R4 2 ERJ-3EKF1000: 100 _ PANASONIC RC0603FR-07100RL 31 R6 CRCW060349R9FK VISHAY DALE 49.9 RESISTOR: 0603; 49.9Q; 1%; 100PPM; 0.10W; THICK FILM 1 CRCW06033K32FK 32 VISHAY DALE RESISTOR: 0603: 3.32K: 1%: 100PPM: 0.10W: THICK FILM R7 _ 1 3.32K CRCW06030000ZS; VISHAY DALE:ROHM: R8. R12 33 4 MCR03EZPJ000; 0 RESISTOR; 0603; 0Ω; 0%; JUMPER; 0.10W; THICK FILM R16. R17 PANASONIC ERJ-3GEY0R00 34 ERJ-8CWFR043 PANASONIC 0.043 RESISTOR; 1206; 0.043Ω; 1%; 75PPM; 1W; THICK FILM R9 1 35 R10 CRCW0603475KFK VISHAY DALE 475K RESISTOR: 0603: 475KQ: 0.1%: 100PPM: 0.1W: THICK FILM CRCW060310K0FK: VISHAY DALE: 36 R11 10K RESISTOR: 0603: 10K: 1%: 100PPM: 0.10W: THICK FILM _ 1 ERJ-3EKF1002 PANASONIC 37 R13 1 CRCW06033K00FK VISHAY DALE 3K RESISTOR; 0603; 3KQ; 1%; 100PPM; 0.10W; THICK FILM 38 R14 1 LRC-LR2512LF-01-R250F TT ELECTRONICS 0.25 RESISTOR; 2512; 0.25Ω; 1%; 100PPM; 2W; THICK FILM _ R15 CRCW06031M00JN RESISTOR; 0603; 1MQ; 5%; 200PPM; 0.10W; METAL FILM 39 VISHAY DALE 1M 1 _ 40 R19 RESISTOR; 0603; 20KQ; 5%; 200PPM; 0.10W; METAL FILM CRCW060320K0JN VISHAY DALE 20K 41 R21 1 ERA-V15J100V PANASONIC 10 RESISTOR; 0603; 10Ω; 5%; 1500PPM; 0.063W; METAL FILM 42 R22 1 LRC-LR1206LF-01-R100-F TT ELECTRONICS RESISTOR: 1206: 0.1Q: 1%: 100PPM: 0.5W: THICK FILM 0.1 43 R23, R25 2 ERJ-3GEYJ102V PANASONIC 1K RESISTOR; 0603; 1KΩ; 5%; 200PPM; 0.10W; THICK FILM 44 R24 301-10K-RC XICON 10K RESISTOR, 0603, 10KQ, 5%, 200PPM, 1/16W, THICK FILM 1 45 R26 FR.I-3GFY.I472V PANASONIC RESISTOR: 0603; 4.7KQ: 5%; 200PPM; 0.10W; THICK FILM _ 1 4.7K TEST POINT; JUMPER; STR; TOTAL LENGTH = 0.24IN; 46 SU1-SU3 3 S1100-B;SX1100-B KYCON;KYCON SX1100-B BLACK; INSULATION = PBT; PHOSPHOR BRONZE CONTACT = GOLD PLATED CONNECTOR; PANELMOUNT; BINDING POST; 47 TP1 7006 KEYSTONE 7006 _ 1 STRAIGHT THROUGH: 1PIN: RED CONNECTOR; PANELMOUNT; BINDING POST; 48 TP2 KEYSTONE 1 7007 7007 _ STRAIGHT THROUGH: 1PIN: BLACK EVKIT PART - IC; MAX25611ATC; 49 U1 MAX25611ATC ΜΔΧΙΜ MAX25611ATC PACKAGE OUTLINE DRAWING: 21-0139 LAND PATTERN DRAWING: 90-0068; TQFN16-EP PCB MAXIM 50 MAX25611 PCB PCB:MAX25611 51 C18 DNP 0 C0805C104J1RAC KEMET 0.1UF CAP; SMT (0805); 0.1UF; 5%; 100V; X7R; CERAMIC CHIP DIODES DIODE; SWT; SMT (SOD-123); PIV = 100V; 52 D3 DNP 0 1N4148W-7-F 1N4148W-7-F INCORPORATED IF = 0.3A; -65°C TO +150°C 53 R5 DNP 0 ERJ-8CWFR043 PANASONIC 0.043 RESISTOR; 1206; 0.043Ω; 1%; 75PPM; 1W; THICK FILM 54 DNP R20 0 CRCW0603499KFK VISHAY DALE 499K RESISTOR: 0603: 499KO: 1%: 100PPM: 0.1W: THICK FILM 55 R27 DNP 0 CRCW0603220RFK VISHAY DALE 220 RESISTOR; 0603; 220Ω; 1%; 100PPM; 0.10W; THICK FILM 56 R28 DNP 0 CRCW060360K4FK VISHAY DALE 60.4K RESISTOR, 0603, 60.4KQ, 1%, 100PPM, 0.1W, THICK FILM TOTAL 80

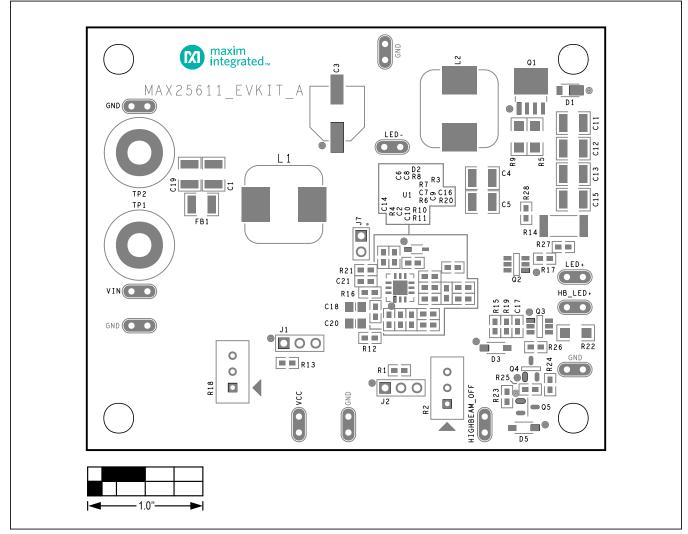
MAX25611 EV Kit Bill of Materials (continued)

Evaluates: MAX25611A/MAX25611B/ MAX25611C/MAX25611D



MAX25611 EV Kit Schematics

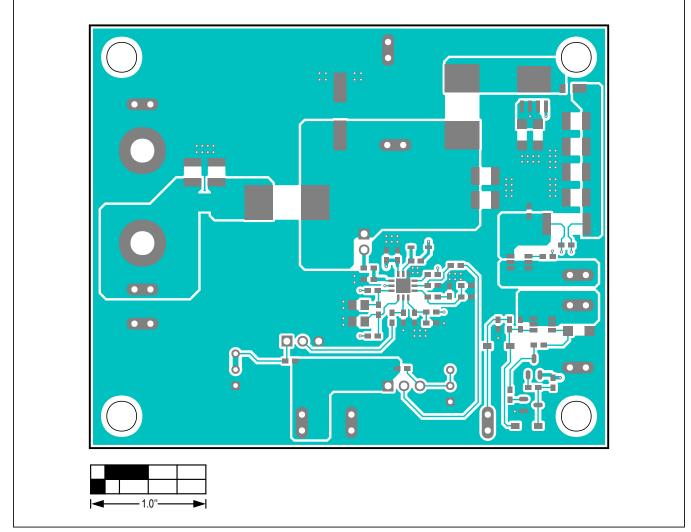
Evaluates: MAX25611A/MAX25611B/ MAX25611C/MAX25611D



MAX25611 EV Kit PCB Layout Diagrams

MAX25611 EV Kit Component Placement Guide—Top Silkscreen

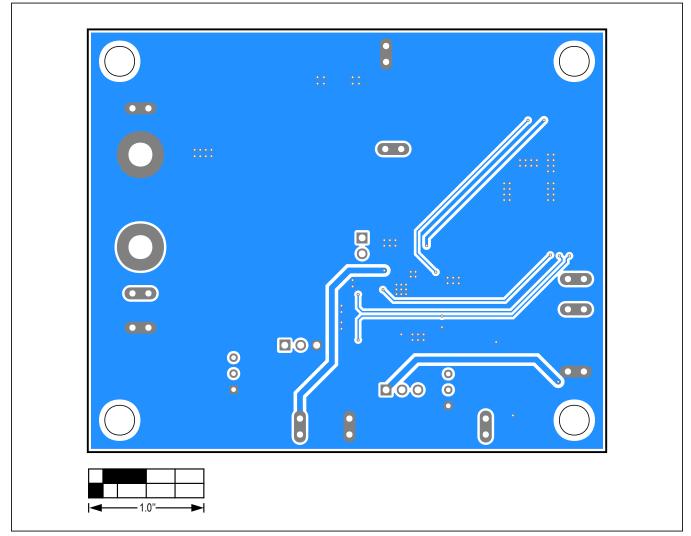
Evaluates: MAX25611A/MAX25611B/ MAX25611C/MAX25611D



MAX25611 EV Kit PCB Layout Diagrams (continued)

MAX25611 EV Kit PCB Layout—Top View

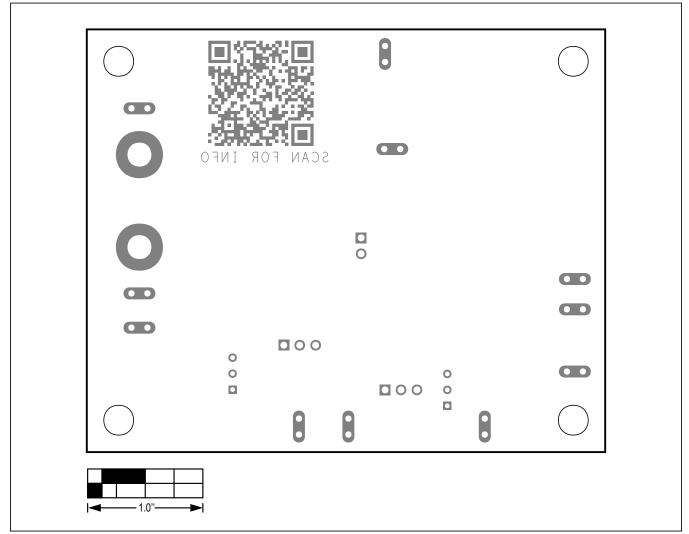
Evaluates: MAX25611A/MAX25611B/ MAX25611C/MAX25611D



MAX25611 EV Kit PCB Layout Diagrams (continued)

MAX25611 EV Kit PCB Layout—Bottom View

Evaluates: MAX25611A/MAX25611B/ MAX25611C/MAX25611D



MAX25611 EV Kit PCB Layout Diagrams (continued)

MAX25611 EV Kit Component Placement Guide—Bottom Silkscreen